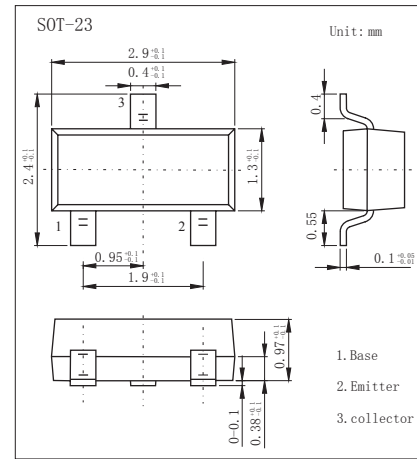


**PNP Transistors**

**BC807**

■ Features

- Ideally suited for automatic insertion
- Epitaxial planar die construction
- Complementary NPN type available(BC817)



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-50	V
Collector - Emitter Voltage	$V_{CE0}$	-45	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_C$	-0.5	A
Collector Power Dissipation	$P_C$	0.3	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = -10\text{ mA}, I_B = 0$	-45			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -45\text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector- emittercut-off current	$I_{CE0}$	$V_{CE} = -40\text{ V}, I_B = 0$			-0.2	
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -4\text{ V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$			-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$			-1.2	
DC current gain	$h_{fe} (1)$	$V_{CE} = -1\text{ V}, I_C = -100\text{ mA}$	100		630	
	$h_{fe} (2)$	$V_{CE} = -1\text{ V}, I_C = -500\text{ mA}$	40			
Transition frequency	$f_T$	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}, f = 100\text{ MHz}$	100			MHz

■ Classification of  $h_{fe}(1)$

Rank	BC807-16	BC807-25	BC807-40
Range	100-250	160-400	250-630
Marking	5A	5B	5C



炬芯微  
XUANXINWEI

SMD Type Transistors

PNP Transistors  
BC807

Typical Characteristics

